L Number	Hits	Search Text	DB	Time stamp
1	424	"front opening unified pod"	USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:35
2	0	"front open unified pod" and "front opening interface mechanical standards"	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28
3	1	"front open unified pod" and FIMS	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:31
4	70	"front open unified pod"	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:32
5	6	"front open unified pod" and JIG	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:34
6	0	"front open unified pod" and JIG and purg\$4	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:34
· 7	0	"front open unified pod" and JIG and gas	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:34
8	66	"front opening unified pod" and purg\$4	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:35
9	59	"front opening unified pod" and purg\$4 and gas	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:37
10	12	"front opening unified pod" and purg\$4" and gas and gap	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/28 09:37
-	18890	(wafer or semiconductor or substrate) and JIG	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/26 10:36
-	264	(wafer or semiconductor or substrate) and JIG and purg\$4	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/10/26 10:36
-	199	(wafer or semiconductor or substrate) and JIG and purg\$4 and gas	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/26 10:36
-	125	(wafer or semiconductor or substrate) and JIG and purg\$4 and gas and atmosphere	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/26 10:36
-	19	(wafer or semiconductor or substrate) and JIG and purg\$4 and gas and atmosphere and open\$4 and clos\$4 and door	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/26 10:44
-	1	(wafer or semiconductor or substrate) and JIG and purg\$4 and gas and atmosphere and open\$4 and clos\$4 and door and FIMS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/26 10:55
-	151	(wafer or semiconductor or substrate) and FIMS	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/26 10:55

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-	5	(wafer or semiconductor or substrate) and		2004/10/26
		FIMS and JIG	US-PGPUB;	10:55
l			EPO; JPO;	
			DERWENT	
i <b>-</b>	5	(wafer or semiconductor or substrate) and	USPAT;	2004/10/26
		FIMS and JIG and door and open\$4 and	US-PGPUB;	10:56
		clos\$4	EPO; JPO;	
			DERWENT	
-	1	(wafer or semiconductor or substrate) and	USPAT;	2004/10/26
		FIMS and JIG and door and open\$4 and	US-PGPUB;	10:56
		clos\$4 and purg\$4 and gas	EPO; JPO;	
			DERWENT	
-	2	(wafer or semiconductor or substrate) and	USPAT;	2004/10/26
		FIMS and JIG and door and open\$4 and	US-PGPUB;	12:46
		clos\$4 and gas	EPO; JPO;	
			DERWENT	
-	2	(purg\$3 adj gas) with door and JIG	USPAT;	2004/10/26
i		•	US-PGPUB;	13:00
			EPO; JPO;	
			DERWENT	
-	1	(purg\$3 adj gas) with door and FIMS	USPAT;	2004/10/26
			US-PGPUB;	13:01
	1	·	EPO; JPO;	
			DERWENT	
-	71	(purg\$3 adj gas) with door	USPAT;	2004/10/26
		,	US-PGPUB;	13:05
			EPO; JPO;	·
		·	DERWENT	
-	49	(purg\$3 adj gas) with door and (substrate	USPAT;	2004/10/26
		or semiconductor or wafer)	US-PGPUB;	13:06
•			EPO; JPO;	
			DERWENT	
-	41	(purg\$3 adj gas) with door and (substrate	USPAT;	2004/10/26
		or semiconductor or wafer) and open\$4 and	US-PGPUB;	13:06
		clos\$4	EPO; JPO;	
			DERWENT	0004/10/05
-	14	(purg\$3 adj gas) with door and (substrate	USPAT;	2004/10/26
		or semiconductor or wafer) and open\$4 and	US-PGPUB;	13:41
		clos\$4 and gap	EPO; JPO;	
			DERWENT	2004/10/20
_	1844	(purg\$3 with gas) and (gas with (gap or	USPAT;	2004/10/26
		door))	US-PGPUB;	13:42
	[		EPO; JPO;	
	1	/	DERWENT	2004/10/26
-	1047		USPAT;	2004/10/26
		door)) and (wafer or semiconductor or	US-PGPUB; EPO; JPO;	13:42
		substrate)		
	777	(	DERWENT	2004/10/26
1 -	777	(purg\$3 with gas) and (gas with (gap or door)) and (wafer or semiconductor or	USPAT; US-PGPUB;	13:44
		substrate) and open\$4 and clos\$4	EPO; JPO;	13.77
1		substrate; and opensa and crossa	DERWENT	
1	,	(nungt? with gas) and (gas with (gan on	USPAT;	2004/10/26
-	1	(purg\$3 with gas) and (gas with (gap or	US-PGPUB;	13:44
	1	door)) and (wafer or semiconductor or substrate) and open\$4 and clos\$4 and jig	EPO; JPO;	12.44
1		and fims	DERWENT	
	21	1	USPAT;	2004/10/26
-	21	(purg\$3 with gas) and (gas with (gap or door)) and (wafer or semiconductor or	US-PGPUB;	13:44
		substrate) and open\$4 and clos\$4 and jig	EPO; JPO;	10.33
		substrace, and obenit and crosts and lid	DERWENT	
	L		DEVMENT	<del></del>